

3D-IC/TSV Design

EDA Software Requirements

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EDPS 2011

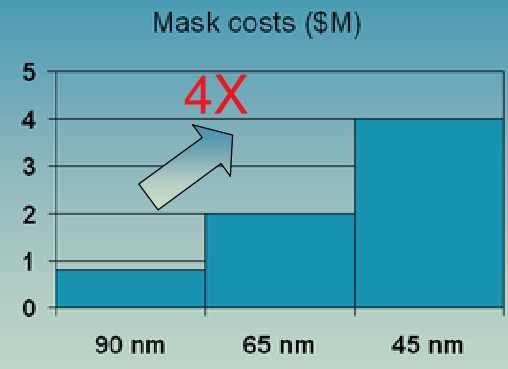


An Inconvenient Truth

“Cost is the New Driver”

Yield and Manufacturability

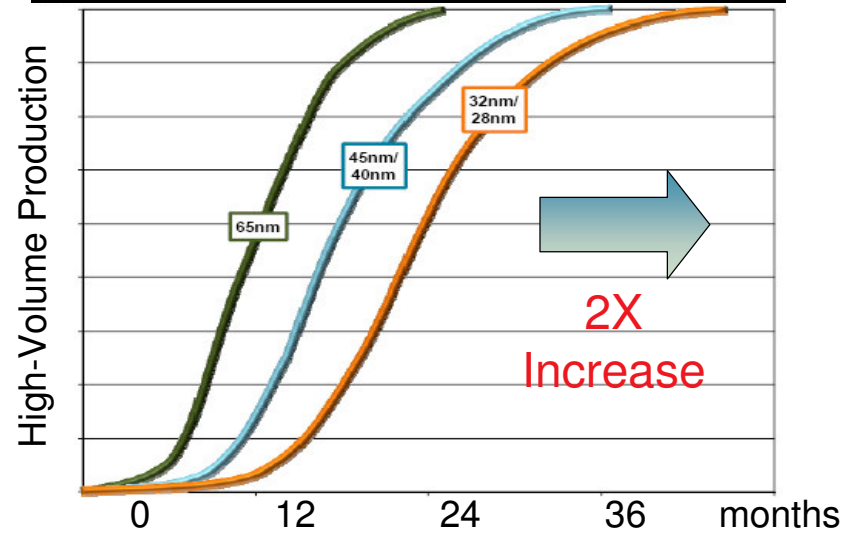
	2005 90 nm	2006 65 nm	2007-2008 45 nm	2009-2010 32 nm
Performance & SI	●	●	●	●
Area	●	●	●	●
Power	●	●	●	●
DFY (Particle Defects)	●	●	●	●
Variation (Device and Interconnect)	●	●	●	●
CMP and Litho		●	●	●
Stress and Etch			●	●
Temperature			●	●
New Devices			●	●



	45-nm node	32-nm node
Fab costs	\$3B	\$5B-10B
Process R&D	\$2.4B	\$3B
Design costs	\$20M-50M	\$75M
Mask costs	\$9M	NA

Source : IBS

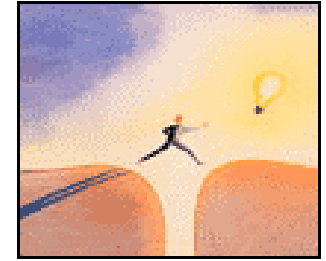
Predictability/Convergence



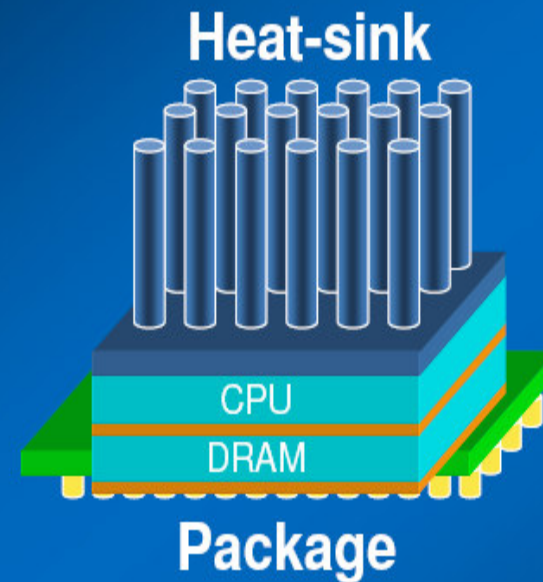
6 month delay causes \$5B in profits!



Why 3D Stacked Dies/TSV?



Integration of Heterogeneous Technologies



Source: Intel

3D technology will help:

1. Integration of heterogeneous technologies
2. Lower interconnect power
3. Lower system cost

Do not want to end up like this!

Increased
SI/Noise
Thermal
Issues

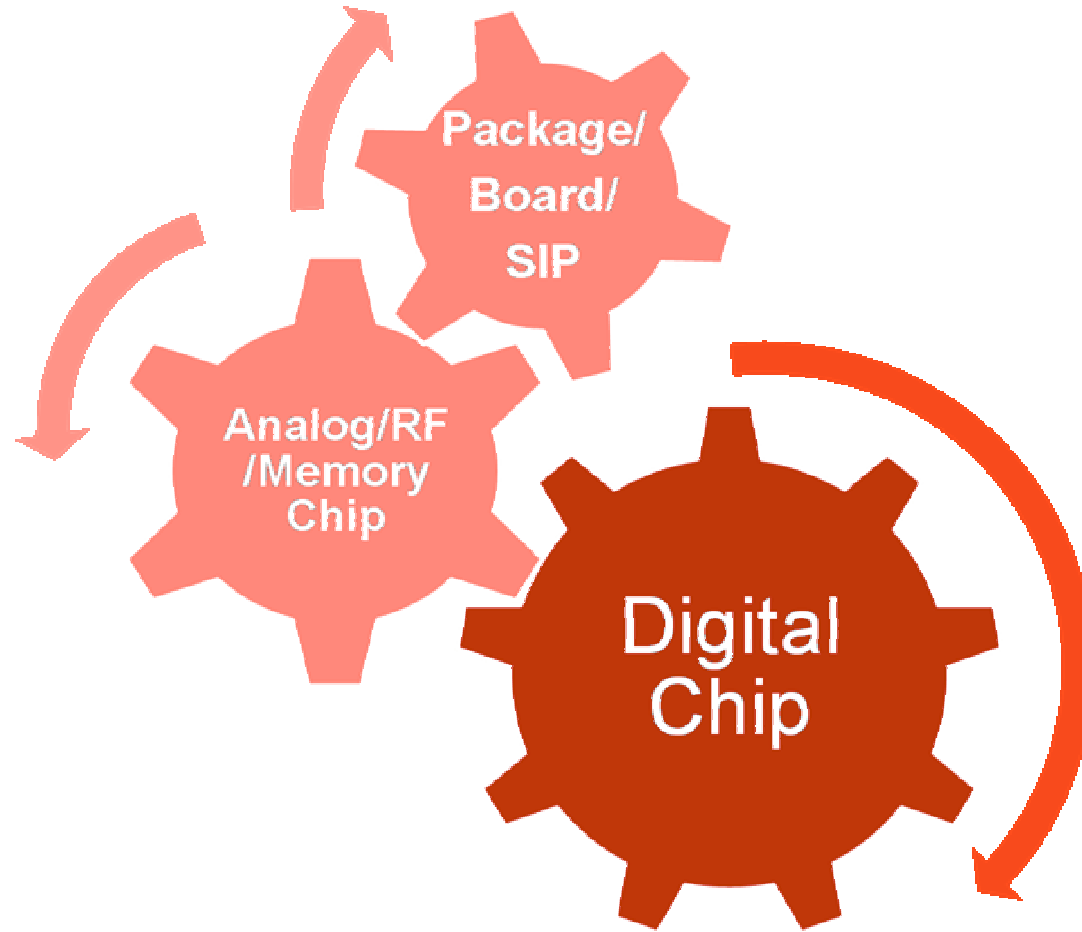
Testing
Reliability
Yield
Issues



3DIC : It is a Heterogeneous Stack

Co-Design of Digital, Analog and Package is Key

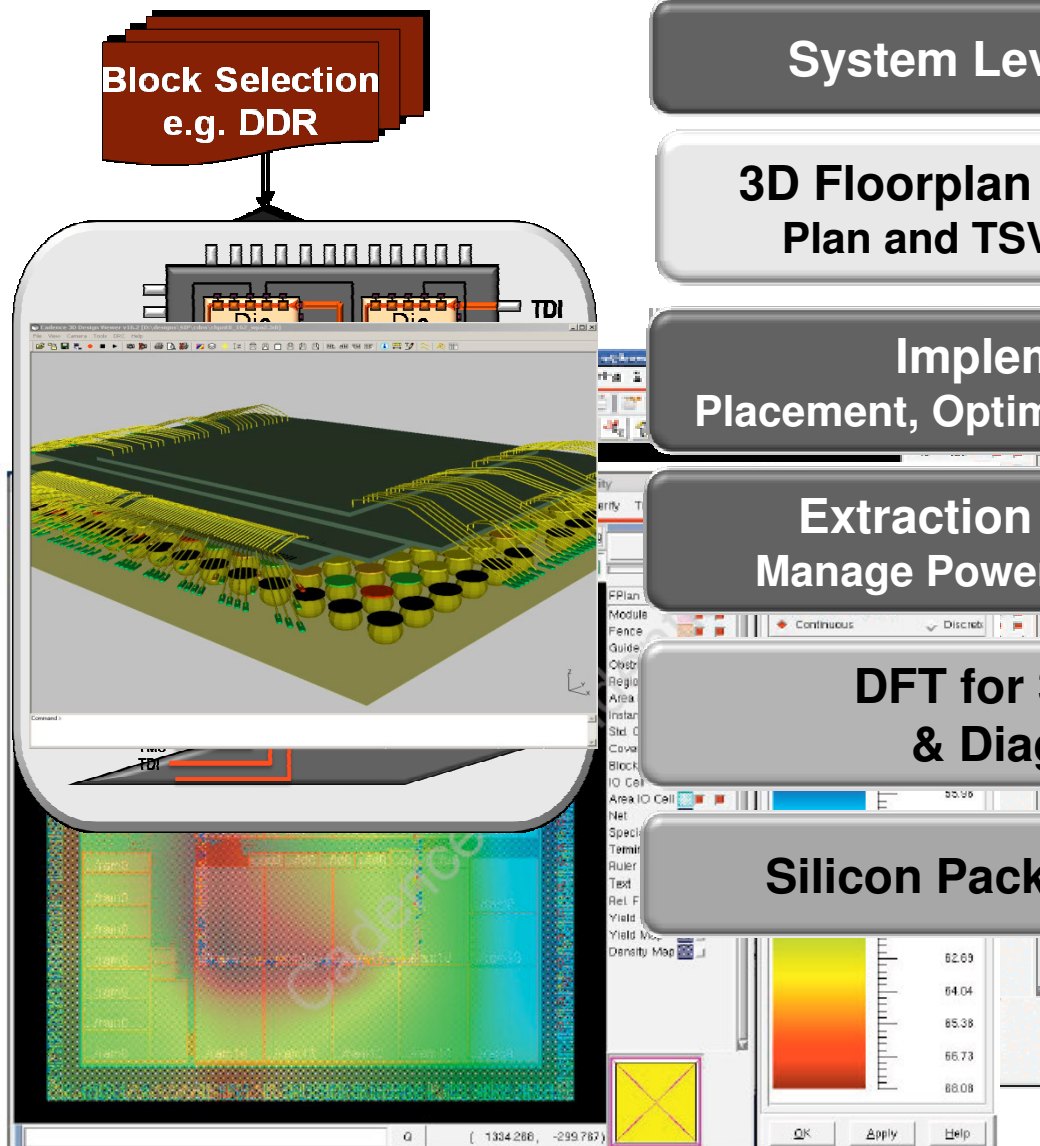
Enabling Heterogeneous System



Closer IC Integration through OA
Co Design is Most essential

3DIC Design Flow Challenges

New 3DIC Design Flow Challenges



System Level Exploration

3D Floorplan – Optimized power Plan and TSV/Bump locations

Implementation
Placement, Optimization and Routing

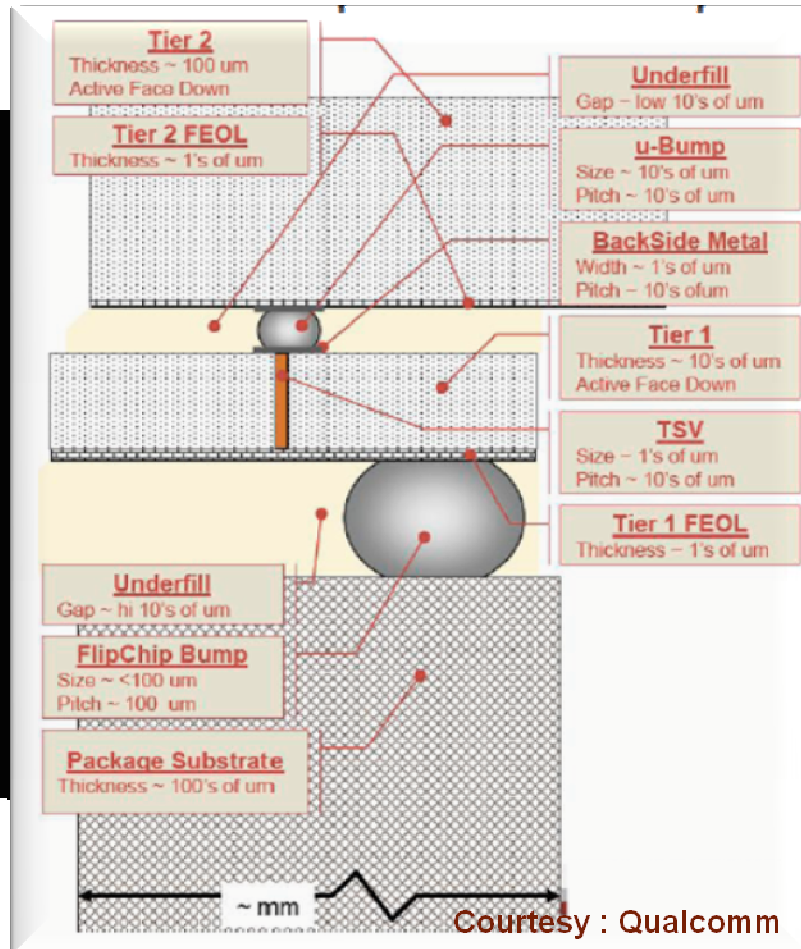
Extraction and Analysis
Manage Power, Thermal and SI

DFT for 3DIC Stack
& Diagnostics

Silicon Package Co-Design

So what changes in the EDA world?

Revamped EDA requirements



New Layout Rules (e.g. alignments)

New Layout Layer (e.g. Back Side RDL)

New Layout & Electrical Feature
(e.g. TSV)

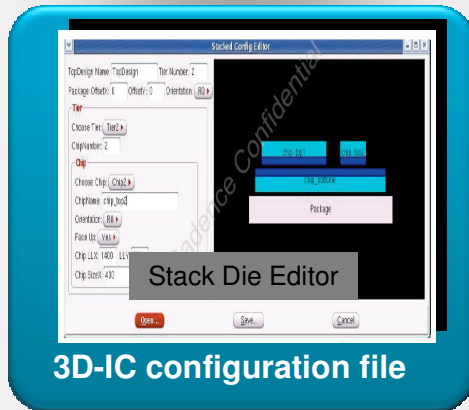
New Floorplanning &
Blockage Rules (TSV)

Thermal & mechanical
constraints

New Models, Rules

Cadence 3DIC Silicon Realization

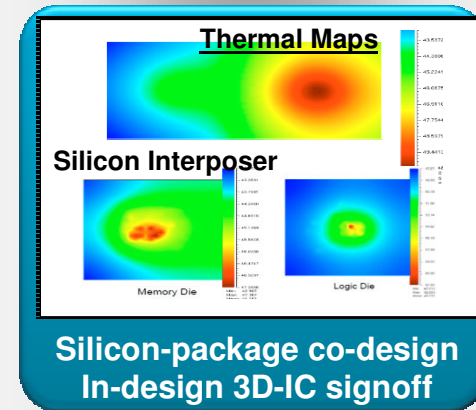
INTENT



ABSTRACTION

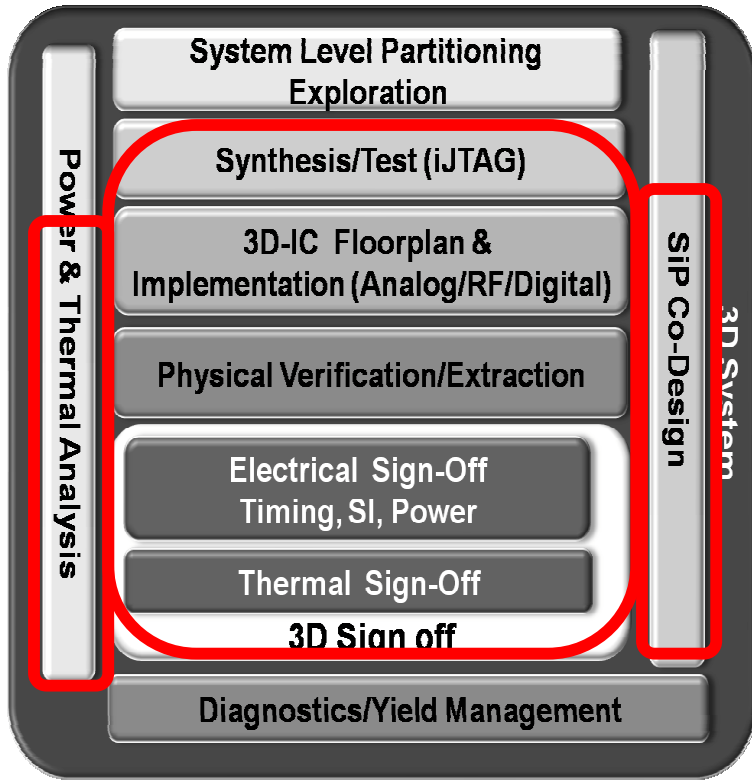


CONVERGENCE



3D-IC EDA Design Tools

Plan->Implement->Test->Verify



Cadence 3D IC Flow

3D Stack Die Editor

3D Floorplan – Optimized power Plan and TSV/Bump locations

TSV /Bump RDL Routing

Virtuoso for custom shape editing

3D IR Drop Analysis

3D Thermal Maps

IC-Package Co design flow Back-side Bump Management

3D view of system in package tool

Back-side bump reading in CDNSIP

Silicon Interposer

Memory Die

Logic Die



3D-IC: Qualcomm + Cadence

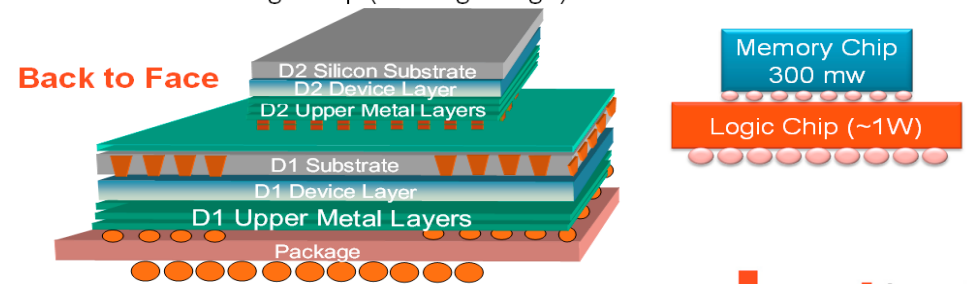
Source: RTI 3D conference 2009 proceedings

Thermal Design Objectives in 3D IC

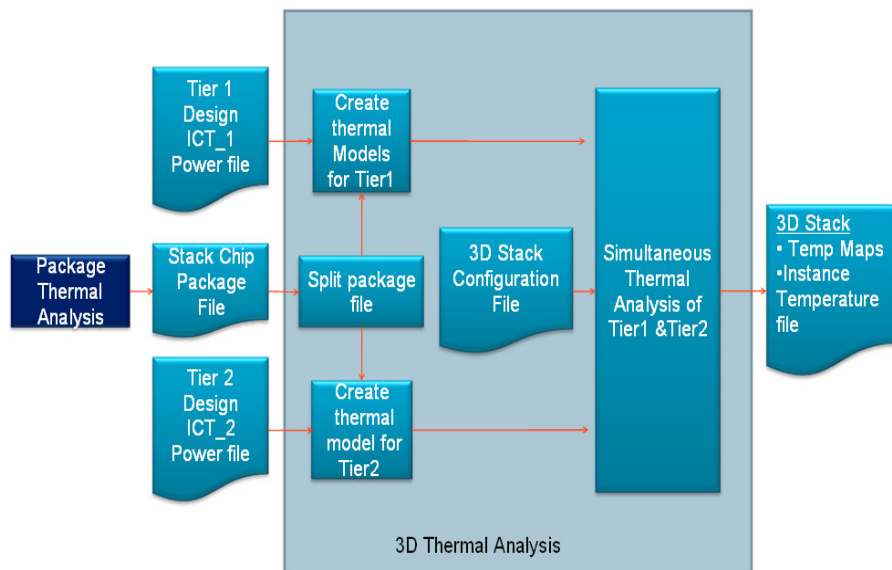
- Communication chip design uses low power techniques (~ 1 Watt). Will stacking low power chip together produce thermal hot spot.
 - We know that microprocessor's power consumption is at least in the 10's of Watts. Stacking with high powered devices have been reported to have thermal challenges in 3D IC.
- If the low power stack does exhibit thermal hot spots:
 - Can regular thermal optimization improve hot spots.
 - Example: Thermal TSV, thermal micro-bumps, better inter-chip material.
 - By how much?
 - Examine other areas to improve on thermal management.

Construction of a Two Chip Stack Design

- EDI (Encounter Digital Implementation) System is used to construct the following stack for thermal management experiments.
 - Memory Chip (Black Box Physical Model)
 - 4 Quadrant of memory banks
 - Four quadrants of micro-bumps.
 - An SOC logic chip (existing design)

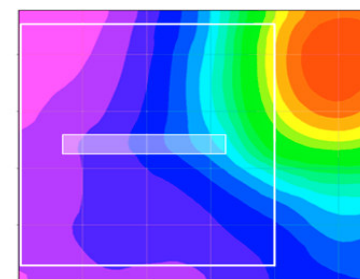


Thermal Analysis Flow For Two Chip TSS

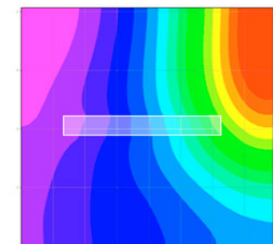


Thermal Gradients

- Significant Thermal Gradients seen across both die
 - 5C to 20C delta across Tier 1 die depending on power scenario
 - Hot spot due to high power block on Tier1 die
 - T1 hot spot vs T2 hot spot temp 3C to 10C depending on power case
 - Thermal coupling between die is very good



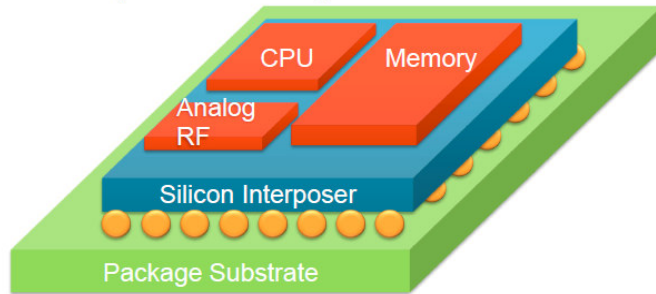
Tier 1 Die



Tier 2 Die

3D-IC: STMicroelectronics + Cadence

Source: RTI 3D conference 2010 proceedings



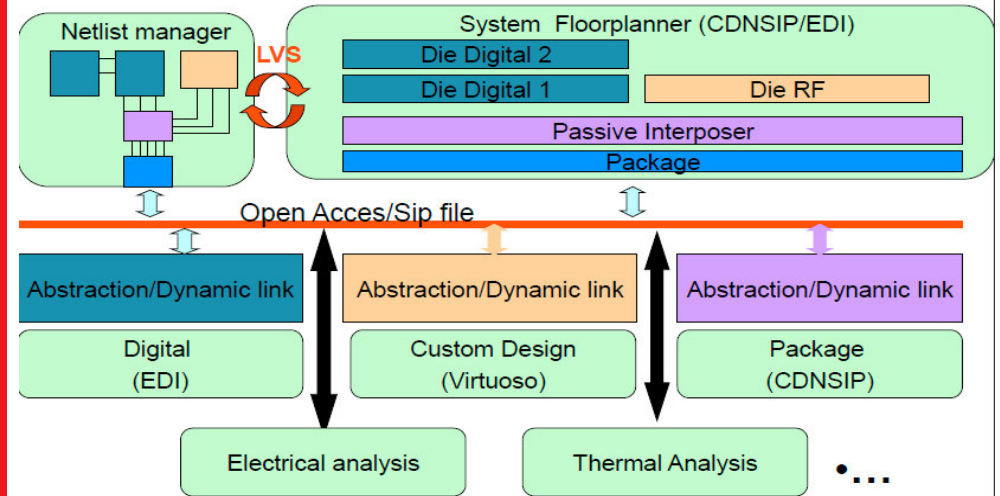
Three chips are placed faced down on top of silicon interposer.

Silicon interposer : 4-9 levels of high density Interconnect.

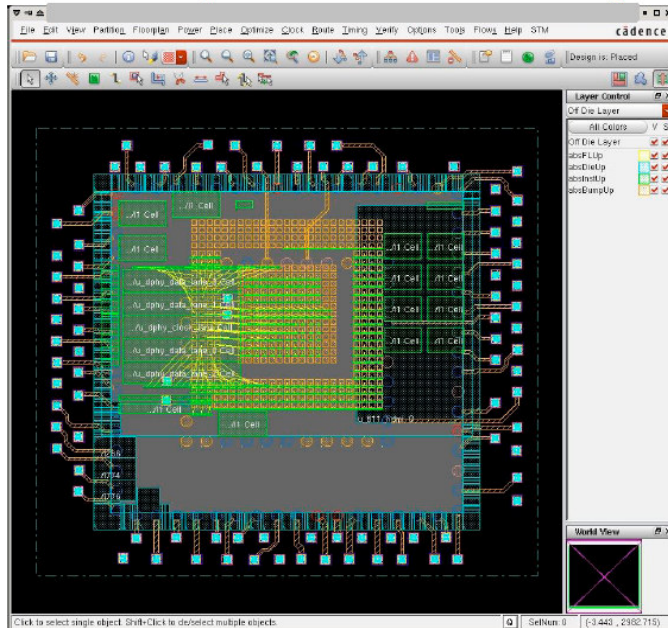
- No active areas.
- Passive devices like metal capacitances.

Challenges: Physical design, electrical analysis, power distribution and analysis and thermal management.

Cadence based ST 3D Solution overview

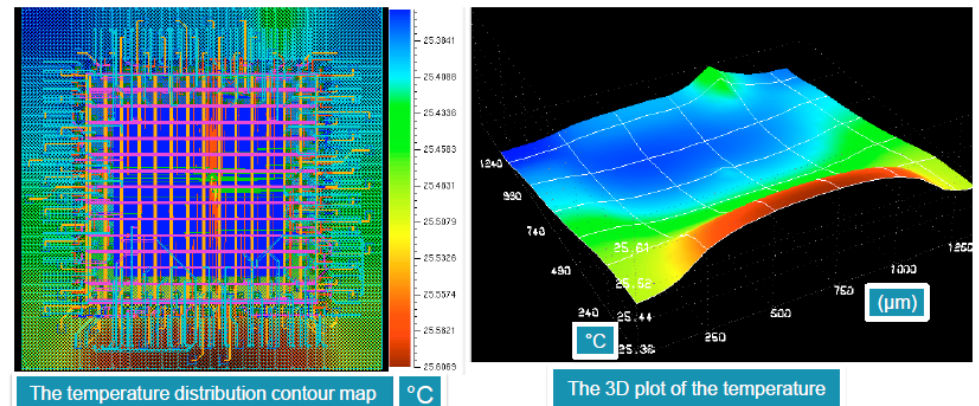


Top view of interposer with TOP die in ghost view



Thermal Analysis Results

- Thermal Analysis Provides a Rich of Thermal Data
 - 2D Thermal contour can be displayed on each chip.
 - 3D Thermal Map.
 - Thermal values per layer and per x,y coordinates.
- The example below has small power consumption → thermal gradient is small

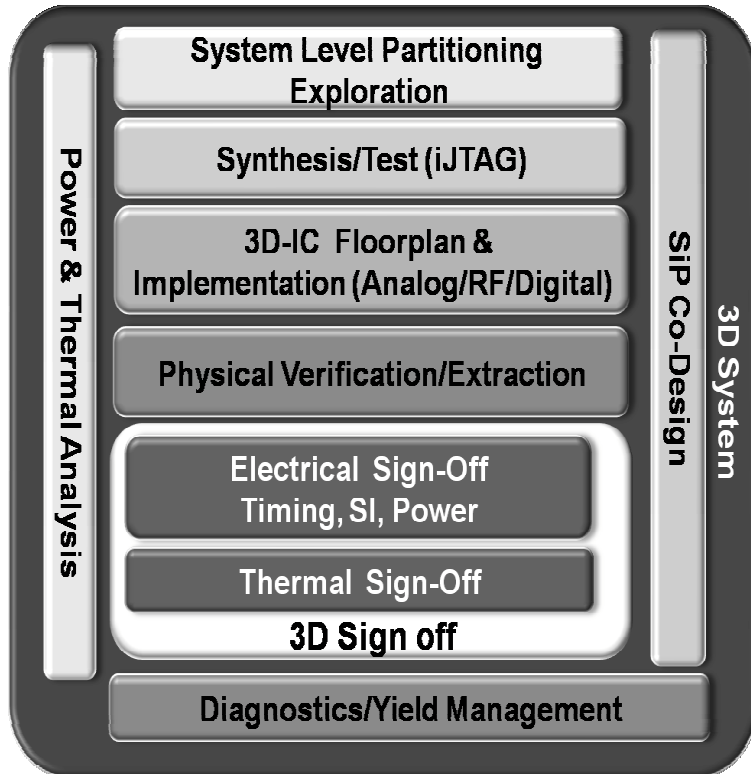


The temperature distribution contour map

The 3D plot of the temperature

Cadence Silicon-Proven 3D-IC Solution

Enabling 3D-IC Silicon Realization



- **Complete, integrated 3D-IC solution**
 - Tools : Plan->Implement->Test->Verify
 - 1st to market 'wide I/O memory controller'
- **Developed in close partner-collaboration**
 - Leading foundries and customers
- **Multiple 3D-IC tapeouts**
 - Memory over logic (28 nm), logic over analog, logic over Logic, 3-stack dies
 - Production design mid-2011 tape-out